General Purpose Transistor

NPN Silicon

- Moisture Sensitivity Level: 1
- ESD Rating: Human Body Model: >4000 V Machine Model: >400 V
- This is a Pb–Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	65	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	۱ _C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	PD	265 2.1	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	470	°C/W
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^{\circ}C$ Derate above 25°C	P _D	640 5.1	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

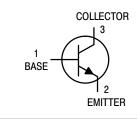
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

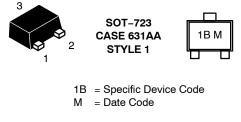


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MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
BC846BM3T5G	SOT-723 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

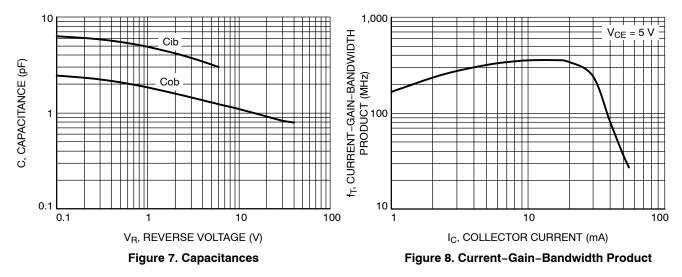
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					-
Collector – Emitter Breakdown Voltage $(I_{C} = 10 \text{ mA})$	V _{(BR)CEO}	65	_	-	V
Collector – Emitter Breakdown Voltage ($I_C = 10 \ \mu A, \ V_{EB} = 0$)	V _{(BR)CES}	80	_	_	V
Collector – Base Breakdown Voltage ($I_C = 10 \ \mu A$)	V _{(BR)CBO}	80	_	_	V
Emitter – Base Breakdown Voltage ($I_E = 1.0 \ \mu A$)	V _{(BR)EBO}	6.0	_	_	V
$ \begin{array}{ll} \mbox{Collector Cutoff Current} & (V_{CB}=30 \mbox{ V}) \\ & (V_{CB}=30 \mbox{ V}, \mbox{ T}_{A}=150^{\circ}\mbox{C}) \end{array} $	I _{CBO}			15 5.0	nA μA
ON CHARACTERISTICS					
DC Current Gain ($I_C = 10 \ \mu A, V_{CE} = 5.0 \ V$) ($I_C = 2.0 \ mA, V_{CE} = 5.0 \ V$)	h _{FE}	_ 200	150 290	_ 450	-
Collector – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) $(I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA})$	V _{CE(sat)}	-	_ _	0.25 0.6	V
Base – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)	V _{BE(sat)}	-	0.7 0.9	_ _	V
$\begin{array}{l} \text{Base-Emitter Voltage (I_C = 1.0 mA, V_{CE} = 5.0 V)} \\ (I_C = 2.0 mA, V_{CE} = 5.0 V) \\ (I_C = 10 mA, V_{CE} = 5.0 V) \end{array}$	V _{BE(on)}	550 580 -	645 660 -	700 700 770	mV
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product ($I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ Vdc}, f = 100 \text{ MHz}$)	f _T	100	_	_	MHz
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)	C _{obo}	_	_	4.5	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	_	_	10	dB

1,000 0.4 150°C ++++ V_{CE(sat)}, COLL-EMIT SATURATION VOLTAGE (V) IC/IB = 20 25°C 0.3 h_{FE}, DC CURRENT -55°C 150°C 100 0.2 25°C 0.1 55°C 10 0 100 0.1 1 10 100 1,000 0.1 10 1 I_C, COLLECTOR CURRENT (mA) IC, COLLECTOR CURRENT (mA) Figure 1. DC Current Gain Figure 2. Collector-Emitter Saturation Voltage V_{BE(on)}, BASE-EMITTER ON VOLTAGE (V) 1.2 1.2 V_{BE(sat)}, BASE-EMIT SATURATION 1.0 1.0 -55°C -55°C 0.8 () 0.0 () 0.4 () 0.8 25 25°C 0.6 150°C 150°C 0.4 0.4 IC/IB = 200.2 $V_{CE} = 5 V$ 0.2 0 0 0.1 10 1,000 0.1 10 100 1,000 1 100 1 I_C, COLLECTOR CURRENT (mA) I_C, COLLECTOR CURRENT (mA) Figure 3. Base-Emitter Saturation Voltage Figure 4. Base-Emitter "On" Voltage V_{CE}, COLLECTOR-EMITTER VOLTAGE (V) TEMPERATURE COEFFICIENT (mV) 2.0 -0.2 = 25°C Τ_A 1 | | | | -0.6 5 V I_C = 200 mA 50 mA 100 mA 20 mA 1.6 10 mA -1.0 1.2 -1.4 -1.8 θ_{VB} , for V_{BE} 0.8 -2.2 0.4 -2.6 θ_{VB} –55°C to 150°C -3.0 0 0.1 10 100 1,000 0.01 100 0.1 10 1 1 I_C, COLLECTOR CURRENT (mA) IB, BASE CURRENT (mA) Figure 5. Base-Emitter Temperature Figure 6. Collector Saturation Region Coefficient

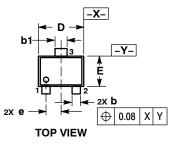
TYPICAL CHARACTERISTICS

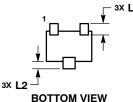
TYPICAL CHARACTERISTICS



PACKAGE DIMENSIONS

SOT-723 CASE 631AA-01 ISSUE D







SIDE VIEW

NOTES:

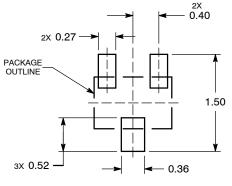
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 1.
- 2. CONTROLLING DIMENSION: MILLIMETERS. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
С	0.07	0.12	0.17
D	1.15	1.20	1.25
Е	0.75	0.80	0.85
е	0.40 BSC		
ΗE	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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